





**SN74LVC7266A** JAJSTI4 - MARCH 2024

# SN74LVC7266A クワッド 2 入力 XNOR ゲート

# 1 特長

- 1.1V~3.6V の動作範囲
- 5.5V 耐圧入力ピン
- 標準ピン配置をサポート
- JESD 17 準拠で 250mA 超のラッチアップ性能
- JESD 22 を上回る ESD 保護
  - 2000V 人体モデル (A114-A)
  - 1000V、荷電デバイス モデル (C101)

# 2 アプリケーション

- パワー グッド信号の結合
- デジタル信号のイネーブル

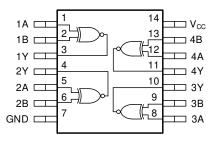
# 3 概要

SN74LVC7266A には、4 つの独立した 2 入力 XNOR ゲートが入っています。各ゲートはブール関数  $Y = \overline{A \oplus B}$ を正論理で実行します。

#### パッケージ情報

部品番号 パッケージ (1)		パッケージ サイズ <sup>(2)</sup>	本体サイズ (公称)(3)
SN74LVC7266A	BQA (WQFN, 14)	3mm × 2.5mm	3mm × 2.5mm
	PW (TSSOP, 14)	5mm × 6.4mm	5mm × 4.4mm

- (1) 詳細については、セクション 11 を参照してください。
- パッケージ サイズ (長さ×幅) は公称値であり、該当する場合はピ ンも含まれます。
- (3) 本体サイズ (長さ×幅) は公称値であり、ピンは含まれません。



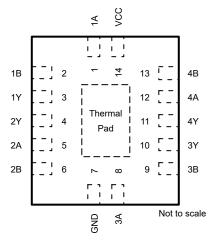
ロジック図



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# **4 Pin Configuration and Functions**



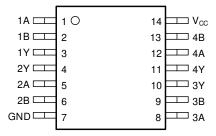


図 4-2. SN74LVC7266A PW Package, 14-Pin TSSOP (Top View)

図 4-1. SN74LVC7266A BQA Package, 14-Pin WQFN (Top View)

表 4-1. Pin Functions

P	IN	TYPE <sup>(1)</sup>	DESCRIPTION
NAME	NO.	I TPE("	DESCRIPTION
1A	1	I	Channel 1, Input A
1B	2	I	Channel 1, Input B
1Y	3	0	Channel 1, Output Y
2Y	4	0	Channel 2, Output Y
2A	5	I	Channel 2, Input A
2B	6	I	Channel 2, Input B
GND	7	_	Ground
3A	8	I	Channel 3, Input A
3B	9	I	Channel 3, Input B
3Y	10	0	Channel 3, Output Y
4Y	11	0	Channel 4, Output Y
4A	12	I	Channel 4, Input A
4B	13	I	Channel 4, Input B
V <sub>CC</sub>	14	_	Positive Supply
Thermal Inform	nation <sup>(2)</sup>	_	The thermal pad can be connected to GND or left floating. Do not connect to any other signal or supply.

- (1) I = input, O = output
- (2) For BQA package only.



# **5 Specifications**

## **5.1 Absolute Maximum Ratings**

over operating free-air temperature range (unless otherwise noted)(1)

				MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage range			-0.5	6.5	V
VI	Input voltage range <sup>(2)</sup>	Input voltage range <sup>(2)</sup>		-0.5	6.5	V
Vo	Output voltage range <sup>(2)</sup>	Output voltage range <sup>(2)</sup>		-0.5	V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	Input clamp current	V <sub>I</sub>	< 0V		-50	mA
I <sub>OK</sub>	Output clamp current	Vo	< 0V		-50	mA
Io	Continuous output current				±50	mA
Io	Continuous output current through	igh V <sub>CC</sub> or GN	ID		±100	mA
TJ	Junction temperature	Junction temperature		-65	150	°C
T <sub>stg</sub>	Storage temperature			-65	150	°C

<sup>(1)</sup> Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If briefly operating outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.

### 5.2 ESD Ratings

			VALUE	UNIT
V <sub>(ESD)</sub> Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	±2000	\/	
	discharge	Charged-device model (CDM), per ANSI/ESDA/JEDEC JS-002 <sup>(2)</sup>	±1000	v

<sup>(1)</sup> JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

### **5.3 Recommended Operating Conditions**

over operating free-air temperature range (unless otherwise noted)

Specifications	Description	Condition	MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage		1.1	3.6	V
VI	Input voltage			5.5	V
Vo	Output voltage	(High or low state)		V <sub>CC</sub>	V
		V <sub>CC</sub> = 1.8V		-4	
	High-level output current	V <sub>CC</sub> = 2.3V		-8	mA
I <sub>OH</sub>	riigii-ievei output current	V <sub>CC</sub> = 2.7V		-12	IIIA
		V <sub>CC</sub> = 3V		-24	
		V <sub>CC</sub> = 1.8V		4	
	Low-level output current	V <sub>CC</sub> = 2.3V		8	mΛ
I <sub>OL</sub>		V <sub>CC</sub> = 2.7V		12	mA
		V <sub>CC</sub> = 3V		24	
Δt/Δν	Input transition rise or fall rate			10	ns/V
T <sub>A</sub>	Operating free-air temperature		-40	125	°C
V <sub>IH</sub>	High-level input voltage	V <sub>CC</sub> = 1.1V	0.75		V
V <sub>IH</sub>	High-level input voltage	V <sub>CC</sub> = 1.5V	0.975		V
V <sub>IH</sub>	High-level input voltage	V <sub>CC</sub> = 1.65V	1.075		V
V <sub>IH</sub>	High-level input voltage	V <sub>CC</sub> = 1.95V	1.2675		V

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<sup>(2)</sup> The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

<sup>(2)</sup> JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

# 5.3 Recommended Operating Conditions (続き)

over operating free-air temperature range (unless otherwise noted)

Specifications	Description	Condition	MIN MAX	UNIT
V <sub>IH</sub>	High-level input voltage	V <sub>CC</sub> = 2.3V	1.7	V
V <sub>IH</sub>	High-level input voltage	V <sub>CC</sub> = 2.7V	1.7	V
V <sub>IH</sub>	High-level input voltage	V <sub>CC</sub> = 3.6V	2	V
V <sub>IL</sub>	Low-Level input voltage	V <sub>CC</sub> = 1.1V	0.40	V
V <sub>IL</sub>	Low-Level input voltage	V <sub>CC</sub> = 1.5V	0.525	V
V <sub>IL</sub>	Low-Level input voltage	V <sub>CC</sub> = 1.65V	0.5775	V
V <sub>IL</sub>	Low-Level input voltage	V <sub>CC</sub> = 1.95V	0.6825	V
V <sub>IL</sub>	Low-Level input voltage	V <sub>CC</sub> = 2.3V	0.7	V
V <sub>IL</sub>	Low-Level input voltage	V <sub>CC</sub> = 2.7V	0.7	V
V <sub>IL</sub>	Low-Level input voltage	V <sub>CC</sub> = 3.6V	3.0	3 V

### **5.4 Thermal Information**

		Package	Package Options			
	THERMAL METRIC <sup>(1)</sup>	PW (TSSOP)	BQA (WQFN)	UNIT		
		14 PINS	14 PINS			
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	150.8	102.3	°C/W		
R <sub>0</sub> JC(top)	Junction-to-case (top) thermal resistance	78.3	96.8	°C/W		
R <sub>θJB</sub>	Junction-to-board thermal resistance	93.8	70.9	°C/W		
$\Psi_{JT}$	Junction-to-top characterization parameter	24.7	16.6	°C/W		
Y <sub>JB</sub>	Junction-to-board characterization parameter	93.2	70.9	°C/W		
R <sub>θJC(bot)</sub>	Junction-to-case (bottom) thermal resistance	-	50.1	°C/W		

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

### 5.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V	-40°C to	-40°C to 125°C		
PARAMETER	TEST CONDITIONS	V <sub>cc</sub>	MIN	TYP	MAX	UNIT
V <sub>OH</sub>	I <sub>OH</sub> = -100μA	1.1V to 3.6V	V <sub>CC</sub> - 0.2			V
V <sub>OH</sub>	I <sub>OH</sub> = -4mA	1.65V	1.2			V
V <sub>OH</sub>	I <sub>OH</sub> = -8mA	2.3V	1.75			V
V <sub>OH</sub>	I <sub>OH</sub> = –12mA	2.7V	2.2			V
V <sub>OH</sub>	IOH IZIIIA	3V	2.4			V
V <sub>OH</sub>	I <sub>OH</sub> = –24mA	3V	2.2			V
V <sub>OL</sub>	I <sub>OH</sub> = 100μA	1.1V to 3.6V			0.15	V
V <sub>OL</sub>	I <sub>OH</sub> = 4mA	1.65V			0.45	V
V <sub>OL</sub>	I <sub>OH</sub> = 8mA	2.3V			0.7	V
V <sub>OL</sub>	I <sub>OH</sub> = 12mA	2.7V			0.4	V
V <sub>OL</sub>	I <sub>OH</sub> = 24mA	3V			0.55	V
I <sub>I</sub>	V <sub>I</sub> = V <sub>CC</sub> or GND	3.6V			±5	μA
I <sub>off</sub>	V <sub>I</sub> or V <sub>O</sub> = V <sub>CC</sub>	0V			±10	μA
Icc	$V_I = V_{CC}$ or GND, $I_O = 0$	3.6V			40	μΑ

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# 5.5 Electrical Characteristics (続き)

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V	-40°C to 125°C			UNIT
PARAMETER	TEST CONDITIONS	V <sub>cc</sub>	MIN	TYP	MAX	UNII
ΔI <sub>CC</sub>	One input at $V_{CC}$ - 0.6V, other inputs at $V_{CC}$ or GND	2.7V to 3.6V			500	μА
Cı	V <sub>I</sub> = V <sub>CC</sub> or GND	3.3V				pF
C <sub>O</sub>	V <sub>O</sub> = V <sub>CC</sub> or GND	3.3V				pF
C <sub>PD</sub>	f = 10MHz	1.8V		31		pF
C <sub>PD</sub>	f = 10MHz	2.5V		31		pF
C <sub>PD</sub>	f = 10MHz	3.3V		32		pF

# **5.6 Switching Characteristics**

over operating free-air temperature range; typical values measured at  $T_A = 25^{\circ}C$  (unless otherwise noted). See *Parameter Measurement Information* 

PARAMETER	FROM	TO (OUTPUT)	LOAD CAPACITANCE	V	-40	°C to 125	s°C	UNIT
PARAMETER	(INPUT)	10 (001701)	LOAD CAPACITANCE	V <sub>cc</sub>	MIN	TYP	MAX	UNII
t <sub>pd</sub>	A or B	Υ	C <sub>L</sub> = 15 pF	1.2V ± 0.1V		12	44	ns
t <sub>pd</sub>	A or B	Υ	C <sub>L</sub> = 15 pF	1.5V ± 0.12V		9	15	ns
t <sub>pd</sub>	A or B	Υ	C <sub>L</sub> = 30 pF	1.8V ± 0.15V			10.2	ns
t <sub>pd</sub>	A or B	Υ	C <sub>L</sub> = 30 pF	2.5V ± 0.2V			6.9	ns
t <sub>pd</sub>	A or B	Υ	C <sub>L</sub> = 50 pF	2.7V			6.4	ns
t <sub>pd</sub>	A or B	Υ	C <sub>L</sub> = 50 pF	3.3V ± 0.3V			5.6	ns
t <sub>sk(o)</sub>				3.3V ± 0.3V			1.5	ns

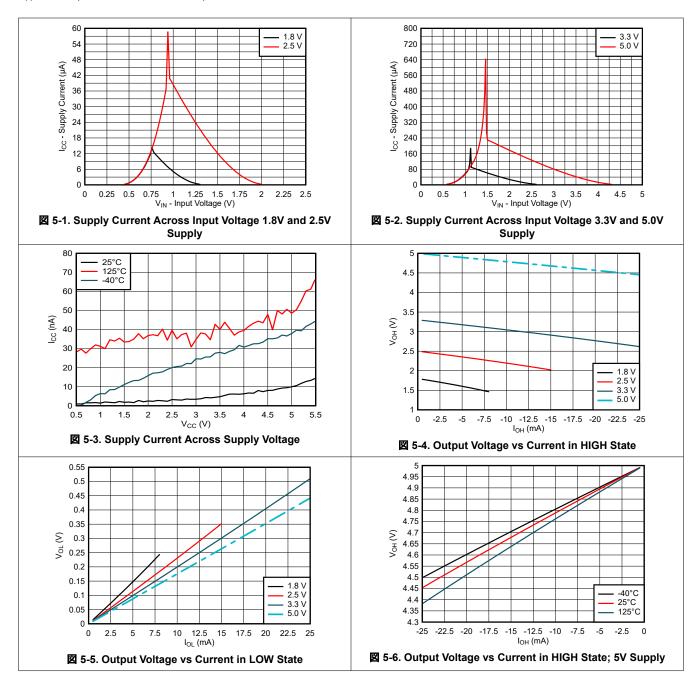
### **5.7 Noise Characteristics**

VCC = 3.3V, CL = 50 pF, TA = 25°C

PARAMETER	DESCRIPTION	MIN	TYP	MAX	UNIT
V <sub>OL(P)</sub>	Quiet output, maximum dynamic V <sub>OL</sub>		0.9	0.8	V
V <sub>OL(V)</sub>	Quiet output, minimum dynamic V <sub>OL</sub>	-0.8	-0.3		V
V <sub>OH(V)</sub>	Quiet output, minimum dynamic V <sub>OH</sub>	2.2	3.3		V
V <sub>IH(D)</sub>	High-level dynamic input voltage	2.0			V
$V_{IL(D)}$	Low-level dynamic input voltage			0.8	V

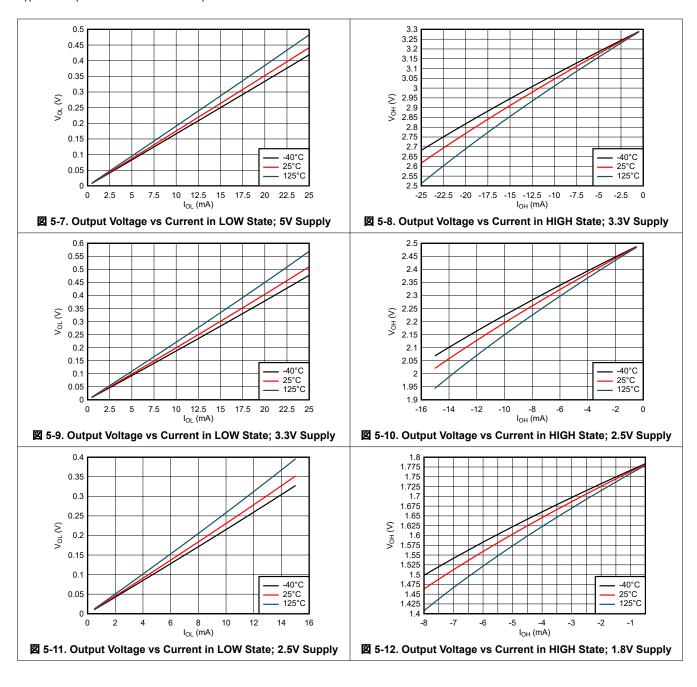
# **5.8 Typical Characteristics**

T<sub>A</sub> = 25°C (unless otherwise noted)



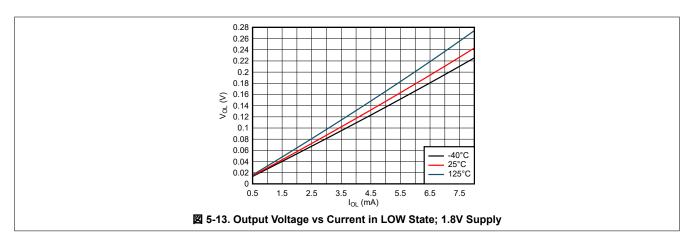
# 5.8 Typical Characteristics (continued)

T<sub>A</sub> = 25°C (unless otherwise noted)



# **5.8 Typical Characteristics (continued)**

T<sub>A</sub> = 25°C (unless otherwise noted)



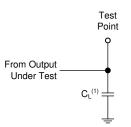


## **6 Parameter Measurement Information**

Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics:  $PRR \le 1MHz$ ,  $Z_O = 50\Omega$ .

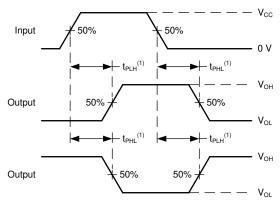
For clock inputs,  $f_{\text{max}}$  is measured when the input duty cycle is 50%.

The outputs are measured one at a time with one input transition per measurement.



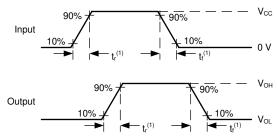
(1)  $C_L$  includes probe and test-fixture capacitance.

図 6-1. Load Circuit for Push-Pull Outputs



(1) The greater between  $t_{PLH}$  and  $t_{PHL}$  is the same as  $t_{pd}$ .

図 6-2. Voltage Waveforms Propagation Delays



(1) The greater between  $t_r$  and  $t_f$  is the same as  $t_t$ .

図 6-3. Voltage Waveforms, Input and Output Transition Times

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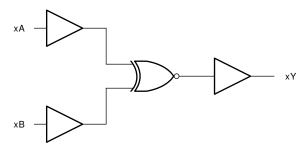
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# 7 Detailed Description

### 7.1 Overview

This device contains four independent 2-input XNOR gates. Each gate performs the Boolean function  $Y = \overline{A \oplus B}$  in positive logic.

# 7.2 Functional Block Diagram



## 7.3 Feature Description

## 7.3.1 Balanced CMOS Push-Pull Outputs

A balanced output allows the device to sink and source similar currents. The drive capability of this device may create fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

The SN74LVC7266A can drive a load with a total capacitance less than or equal to the maximum load listed in the *Switching Characteristics* connected to a high-impedance CMOS input while still meeting all of the datasheet specifications. Larger capacitive loads can be applied, however it is not recommended to exceed the provided load value. If larger capacitive loads are required, it is recommended to add a series resistor between the output and the capacitor to limit output current to the values given in the *Absolute Maximum Ratings*.



#### 7.3.2 Standard CMOS Inputs

This device includes standard CMOS inputs. Standard CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the Electrical Characteristics. The worst case resistance is calculated with the maximum input voltage, given in the Absolute Maximum Ratings, and the maximum input leakage current, given in the Electrical Characteristics, using Ohm's law (R = V ÷ I).

Standard CMOS inputs require that input signals transition between valid logic states quickly, as defined by the input transition time or rate in the Recommended Operating Conditions table. Failing to meet this specification will result in excessive power consumption and could cause oscillations. More details can be found in Implications of Slow or Floating CMOS Inputs.

Do not leave standard CMOS inputs floating at any time during operation. Unused inputs must be terminated at V<sub>CC</sub> or GND. If a system will not be actively driving an input at all times, then a pull-up or pull-down resistor can be added to provide a valid input voltage during these times. The resistor value will depend on multiple factors; a  $10k\Omega$  resistor, however, is recommended and will typically meet all requirements.

#### 7.3.3 Clamp Diode Structure

#### 注意

Voltages beyond the values specified in the Absolute Maximum Ratings table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clampcurrent ratings are observed.

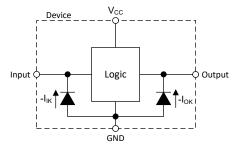


図 7-1. Electrical Placement of Clamping Diodes for Each Input and Output

#### 7.4 Device Functional Modes

表 7-1. Function Table

INP	OUTPUT	
Α	В	Y
L	L	Н
L	Н	L
Н	L	L
Н	Н	Н

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## 8 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

### 8.1 Application Information

In this application, a 2-input XNOR gate is used as a phase difference detector as shown in  $\boxtimes$  8-1. The remaining three gates can be used for other applications in the system, or the inputs can be grounded and the channels left unused.

The device is used to identify phase difference between a reference clock and another input clock. Whenever the clock states are different, the XNOR output will pulse HIGH until the clocks return to the same state. The output is fed into a low-pass filter to obtain a DC representation of the phase difference.

### 8.2 Typical Application

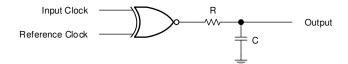


図 8-1. Typical application schematic

#### 8.2.1 Design Requirements

#### 8.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics as described in the *Electrical Characteristics*.

The supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74LVC7266A plus the maximum supply current,  $I_{CC}$ , listed in the *Electrical Characteristics*. The logic device can only source or sink as much current as it is provided at the supply and ground pins, respectively. Be sure not to exceed the maximum total current through GND or  $V_{CC}$  listed in the *Absolute Maximum Ratings*.

Total power consumption can be calculated using the information provided in CMOS Power Consumption and  $C_{pd}$  Calculation.

Thermal increase can be calculated using the information provided in Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices.

#### 注意

The maximum junction temperature, T<sub>J</sub>(max) listed in the *Absolute Maximum Ratings*, is an *additional limitation* to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

### 8.2.1.2 Input Considerations

Input signals must cross  $V_{t-}(min)$  to be considered a logic LOW, and  $V_{t+}(max)$  to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings* .

Unused inputs must be terminated to either  $V_{CC}$  or ground. These can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input is to be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used

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for a default state of LOW. The resistor size is limited by drive current of the controller, leakage current into the SN74LVC7266A, as specified in the *Electrical Characteristics*, and the desired input transition rate. A  $10k\Omega$  resistor value is often used due to these factors.

The SN74LVC7266A has no input signal transition rate requirements because it has Schmitt-trigger inputs.

Another benefit to having Schmitt-trigger inputs is the ability to reject noise. Noise with a large enough amplitude can still cause issues. To know how much noise is too much, please refer to the  $\Delta V_T$ (min) in the *Electrical Characteristics*. This hysteresis value will provide the peak-to-peak limit.

Unlike what happens with standard CMOS inputs, Schmitt-trigger inputs can be held at any valid value without causing huge increases in power consumption. The typical additional current caused by holding an input at a value other than V<sub>CC</sub> or ground is plotted in the *Typical Characteristics*.

Refer to セクション 7.3 for additional information regarding the inputs for this device.

#### 8.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the  $V_{OH}$  specification in the *Electrical Characteristics*. Similarly, the ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the  $V_{OL}$  specification in the *Electrical Characteristics*.

Unused outputs can be left floating. Do not connect outputs directly to V<sub>CC</sub> or ground.

Refer to セクション 7.3 for additional information regarding the outputs for this device.

#### 8.2.2 Detailed Design Procedure

- 1. Add a decoupling capacitor from V<sub>CC</sub> to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V<sub>CC</sub> and GND pins. An example layout is shown in the セクション 8.4.
- 2. Ensure the capacitive load at the output is ≤ 70pF. This is not a hard limit; however, it will optimize performance. This can be accomplished by providing short, appropriately sized traces from the SN74LVC7266A to the receiving device.
- 3. Ensure the resistive load at the output is larger than (V<sub>CC</sub> / I<sub>O</sub>(max)) Ω. This will not violate the maximum output current from the *Absolute Maximum Ratings*. Most CMOS inputs have a resistive load measured in megaohms; much larger than the minimum calculated above.
- 4. Thermal issues are rarely a concern for logic gates, however the power consumption and thermal increase can be calculated using the steps provided in the application report, CMOS Power Consumption and Cpd Calculation

### 8.2.3 Application Curves

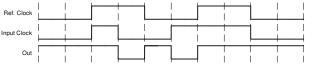


図 8-2. Typical Application Timing Diagram

### 8.3 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each  $V_{CC}$  terminal should have a bypass capacitor to prevent power disturbance. A 0.1µF capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1µF and 1µF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in  $\boxtimes$  8-3.

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### 8.4 Layout

### 8.4.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must never be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V<sub>CC</sub>, whichever makes more sense for the logic function or is more convenient.

#### 8.4.2 Layout Example

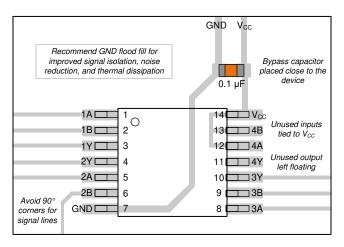


図 8-3. Example Layout for the SN74LVC7266A



## 9 Device and Documentation Support

# 9.1 Documentation Support

#### 9.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, Introduction to Logic application report
- Texas Instruments, Implications of Slow or Floating CMOS Inputs application note

### 9.2 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、www.tij.co.jp のデバイス製品フォルダを開いてください。[通知] をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取ることができます。 変更の詳細については、改訂されたドキュメントに含まれている改訂履歴をご覧ください。

#### 9.3 サポート・リソース

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# 9.5 静電気放電に関する注意事項



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ESD による破損は、わずかな性能低下からデバイスの完全な故障まで多岐にわたります。精密な IC の場合、パラメータがわずかに変化するだけで公表されている仕様から外れる可能性があるため、破損が発生しやすくなっています。

#### 9.6 用語集

テキサス・インスツルメンツ用語集 この用語集には、用語や略語の一覧および定義が記載されています。

## 10 Revision History

DATE	REVISION	NOTES			
March 2024	*	Initial Release			

# 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser based versions of this data sheet, refer to the left hand navigation.

資料に関するフィードバック(ご意見やお問い合わせ) を送信

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#### PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LVC7266ABQAR	ACTIVE	WQFN	BQA	14	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LC726A	Samples
SN74LVC7266APWR	ACTIVE	TSSOP	PW	14	3000	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 125	LVC7266	Samples

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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# **PACKAGE OPTION ADDENDUM**

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#### OTHER QUALIFIED VERSIONS OF SN74LVC7266A:

Automotive: SN74LVC7266A-Q1

NOTE: Qualified Version Definitions:

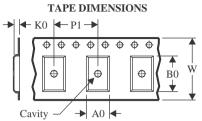
• Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

# **PACKAGE MATERIALS INFORMATION**

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### TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC7266ABQAR	WQFN	BQA	14	3000	180.0	12.4	2.8	3.3	1.1	4.0	12.0	Q1
SN74LVC7266APWR	TSSOP	PW	14	3000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

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### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC7266ABQAR	WQFN	BQA	14	3000	210.0	185.0	35.0
SN74LVC7266APWR	TSSOP	PW	14	3000	356.0	356.0	35.0

2.5 x 3, 0.5 mm pitch

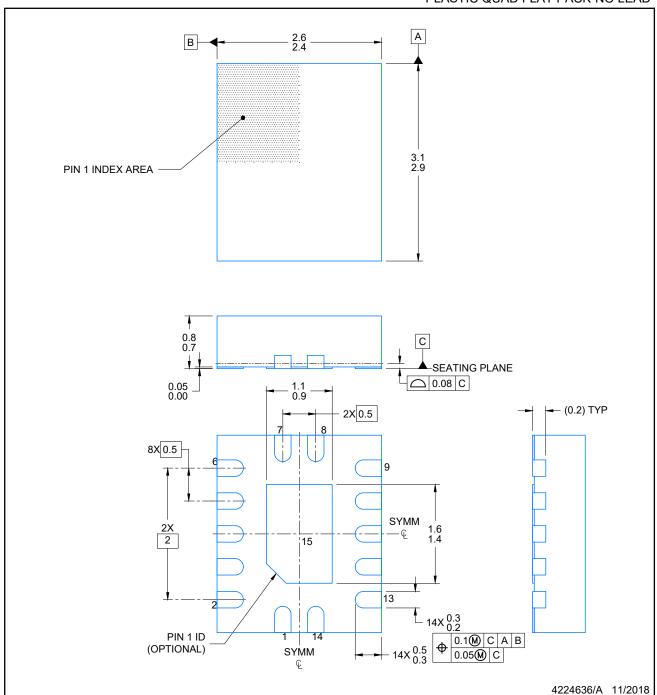
PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



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PLASTIC QUAD FLAT PACK-NO LEAD

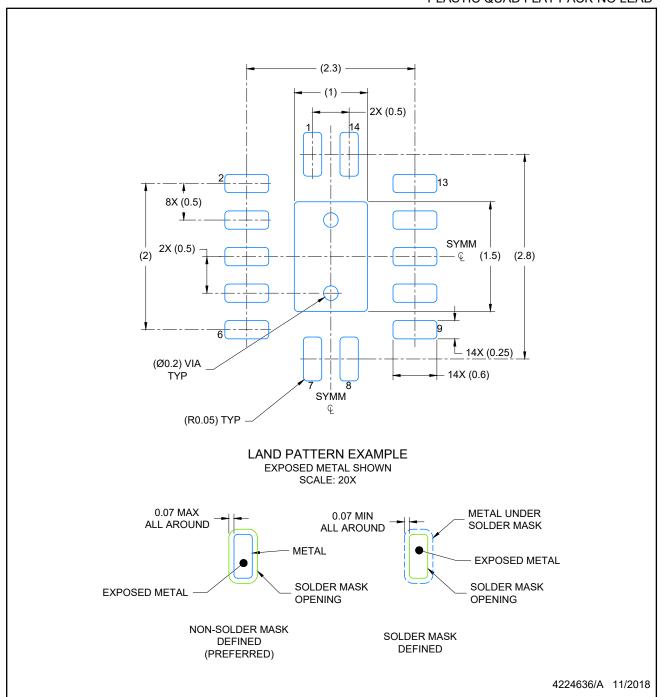


### NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.



PLASTIC QUAD FLAT PACK-NO LEAD

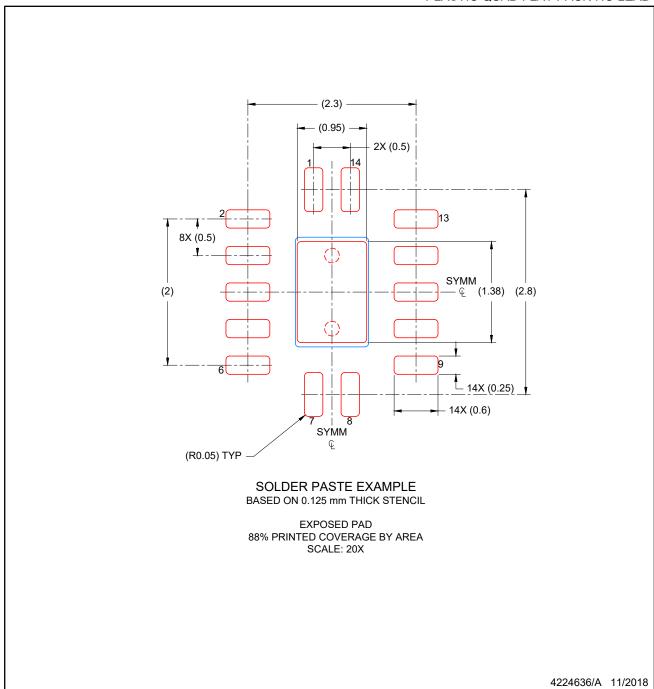


NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



PLASTIC QUAD FLAT PACK-NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



PW (R-PDSO-G14)

# PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153



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